

Description

The BSS214NWH6327 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 20V I_D = 2A$ $R_{DS(ON)} < 55m\Omega@ V_{GS} = 4.5V$ $R_{DS(ON)} < 85m\Omega@ V_{GS} = 2.5V$

Application

Battery protection Load switch Uninterruptible power supply

Package Marking and Ordering Information

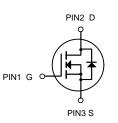
| Product ID | Pack | Brand | Qty(PCS) |
|---------------|---------|------------|----------|
| BSS214NWH6327 | SOT-323 | HXY MOSFET | 3000 |

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

| Symbol | Parameter | Limit | Unit | |
|----------------|--|------------|------|--|
| Vds | Drain-Source Voltage | 20 | V | |
| Vgs | Gate-Source Voltage | ±12 | V | |
| Ι _D | Drain Current-Continuous | 2 | A | |
| PD | Maximum Power Dissipation | 0.3 | W | |
| Tj,Tstg | Operating Junction and Storage Temperature Range | -55 To 150 | °C | |
| Reja | Thermal Resistance, Junction-to-Ambient (Note 2) | 125 | °C/W | |







N-Channel MOSFET



| Electrical Characteristics (T | Γ _A =25℃unless otherwise noted) |
|--------------------------------------|--|
|--------------------------------------|--|

| Parameter | Symbol | Test conditions | Min | Тур | Max | Unit |
|---|----------------------|--|-----|-----|------|------|
| STATIC CHARACTERISTICE | | | | | | |
| Drain-source breakdown voltage | V _{(BR)DSS} | V _{GS} = 0V, I _D =250µA | 20 | | | V |
| Zero gate voltage drain current | I _{DSS} | V _{DS} =18V,V _{GS} = 0V | | | 1 | μA |
| Gate-body leakage current | Igss | V_{GS} =±12V, V_{DS} = 0V | | | ±100 | nA |
| Gate threshold voltage (note2) | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250µA | 0.4 | 0.7 | 1.0 | V |
| | R _{DS(on)} | V _{GS} =4.5V, I _D =2.0A | | | 55 | mΩ |
| Drain-source on-resistance (note2) | | V _{GS} =2.5V, I _D =0.3A | | | 85 | mΩ |
| Maximum Continuous Drain to Source Diode Forward Current | Is | | | | 1.0 | A |
| Diode forward voltage | V _{SD} | I _S =1.0A, V _{GS} =0V | | | 1.2 | V |
| DYNAMIC CHARACTERISTICS (note3) | | | | | | |
| Input capacitance | C _{iss} | | | 300 | | pF |
| Output capacitance | Coss | V _{DS} =10V,V _{GS} =0V, f =1MHz | | 120 | | pF |
| Reverse transfer capacitance | C _{rss} | | | 80 | | pF |
| | te3) | | | | | |
| Turn-on delay time | t _{d(on)} | | | | 15 | nS |
| Turn-on rise time | tr | V _{GS} =4.5V,V _{DS} =10V, | | | 85 | nS |
| Turn-off delay time | t _{d(off)} | R _L =5.1Ω,R _G =5.1Ω | | | 65 | nS |
| Turn-off fall time | t _f | | | | 27 | nS |

Notes:

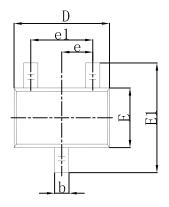
1. Surface mounted on FR4 board using the minimum recommended pad size.

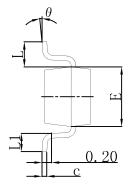
2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.

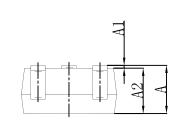
3. These parameters have no way to verify.



SOT-323 Package Outline Dimensions







| Symbol | Dimensions In Millimeters | | Dimensions In Inches | | |
|--------|---------------------------|-------|----------------------|-------|--|
| | Min | Max | Min | Max | |
| A | 0.900 | 1.100 | 0.035 | 0.043 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 0.900 | 1.000 | 0.035 | 0.039 | |
| b | 0.200 | 0.400 | 0.008 | 0.016 | |
| С | 0.080 | 0.150 | 0.003 | 0.006 | |
| D | 2.000 | 2.200 | 0.079 | 0.087 | |
| E | 1.150 | 1.350 | 0.045 | 0.053 | |
| E1 | 2.150 | 2.450 | 0.085 | 0.096 | |
| е | 0.650 TYP | | 0.026 TYP | | |
| e1 | 1.200 | 1.400 | 0.047 | 0.055 | |
| L | 0.525 REF | | 0.021 REF | | |
| L1 | 0.260 | 0.460 | 0.010 | 0.018 | |
| K | 0° | 8° | 0° | 8° | |



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